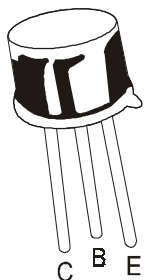


NPN HIGH VOLTAGE SILICON SWITCHING TRANSISTORS

2N3724

2N3725



TO-39

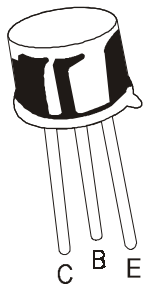
Metal Can Package

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	2N3724	2N3725	UNITS
Collector Emitter Voltage	V_{CEO}	30	50	V
Collector Base Voltage	V_{CBO}	50	80	V
Emitter Base Voltage	V_{EBO}	6.0		V
Collector Current - Continuous	I_C	1.0		A
Power Dissipation @ $T_A=25^\circ\text{C}$	P_D	1.0		W
Derate Above 25°C		5.71		mW/ $^\circ\text{C}$
Power Dissipation @ $T_C=25^\circ\text{C}$	P_D	5.0		W
Derate Above 25°C		28.6		mW/ $^\circ\text{C}$
Operating And Storage Junction Temperature Range	T_j, T_{stg}	- 65 to +200		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	2N3724	2N3725	UNITS
Collector Emitter Voltage	V_{CEO}^*	$I_C=10\text{mA}, I_B=0$	>30	>50	V
Collector Emitter Voltage	V_{CES}	$I_C=10\mu\text{A}, V_{BE}=0$	>50	>80	V
Collector Base Voltage	V_{CBO}	$I_C=10\mu\text{A}, I_E=0$	>50	>80	V
Emitter Base Voltage	V_{EBO}	$I_E=10\mu\text{A}, I_C=0$	>6.0	>6.0	V
Collector Cut Off Current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$	<1.7	-	μA
		$V_{CB}=60\text{V}, I_E=0$	-	<1.7	μA
		$T_A=100^\circ\text{C}$			
		$V_{CB}=40\text{V}, I_E=0$	<120	-	μA
Collector Cut Off Current	I_{CES}	$V_{CE}=50\text{V}, V_{EB}=0$	<10	-	μA
		$V_{CE}=80\text{V}, V_{EB}=0$	-	<10	μA
Base Current	I_B	$V_{CE}=50\text{V}, V_{EB}=0$	<10	-	μA
		$V_{CE}=80\text{V}, V_{EB}=0$	-	<10	μA



TO-39
Metal Can Package

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	2N3724	2N3725	UNITS
DC Current Gain	h_{FE}^*	$I_C=10\text{mA}, V_{CE}=1\text{V}$	>30	>30	
		$I_C=100\text{mA}, V_{CE}=1\text{V}$	60 - 150	60 - 150	
		$I_C=300\text{mA}, V_{CE}=1\text{V}$	>40	>40	
		$I_C=500\text{mA}, V_{CE}=1\text{V}$	>35	>35	
		$I_C=800\text{mA}, V_{CE}=2\text{V}$	>25	>20	
		$I_C=1\text{A}, V_{CE}=5\text{V}$	>30	>25	
		$T_A = -55^\circ\text{C}$			
		$I_C=100\text{mA}, V_{CE}=1\text{V}$	>30	>30	
		$I_C=500\text{mA}, V_{CE}=1\text{V}$	>20	>20	
Collector Emitter Saturation Voltage	$V_{CE(\text{Sat})}^*$	$I_C=10\text{mA}, I_B=1\text{mA}$	<0.25	<0.25	V
		$I_C=100\text{mA}, I_B=10\text{mA}$	<0.20	<0.26	
		$I_C=300\text{mA}, I_B=30\text{mA}$	<0.32	<0.40	
		$I_C=500\text{mA}, I_B=50\text{mA}$	<0.42	<0.52	
		$I_C=800\text{mA}, I_B=80\text{mA}$	<0.65	<0.80	
		$I_C=1\text{A}, I_B=100\text{mA}$	<0.75	<0.95	
Base Emitter Saturation Voltage	$V_{BE(\text{Sat})}^*$	$I_C=10\text{mA}, I_B=1\text{mA}$	<0.76	<0.76	V
		$I_C=100\text{mA}, I_B=10\text{mA}$	<0.86	<0.86	
		$I_C=300\text{mA}, I_B=30\text{mA}$	<1.1	<1.1	
		$I_C=500\text{mA}, I_B=50\text{mA}$	0.8 - 1.1	0.8 - 1.1	
		$I_C=800\text{mA}, I_B=80\text{mA}$	<1.5	<1.5	
		$I_C=1\text{A}, I_B=100\text{mA}$	<1.7	<1.7	

SMALL SIGNAL CHARACTERISTICS

Current Gain Bandwidth Product	$f_{T^{**}}$	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$	>300	>300	MHz
Output Capacitance	C_{obo}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$	<12	<10	pF
Input Capacitance	C_{ibo}	$V_{EB}=0.5\text{V}, I_C=0, f=1\text{MHz}$	<55	<55	pF

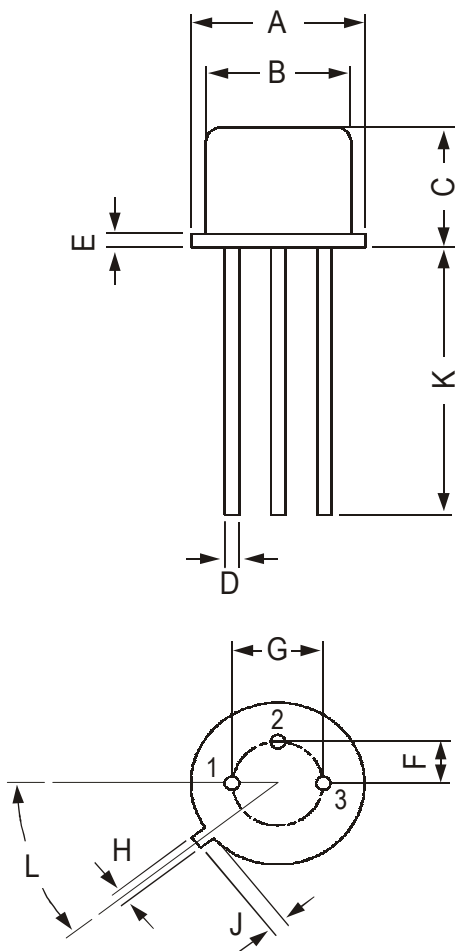
*Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1\%$

** $f_T = |h_{fe}| \cdot f_{\text{test}}$

SWITCHING CHARACTERISTICS

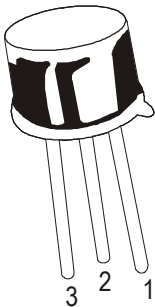
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
Delay Time	t_d	$V_{CC}=30\text{V}, V_{BE}(\text{Off})=3.8\text{V}$	-	10	ns
Rise Time	t_r	$I_C=500\text{mA}, I_{B1}=50\text{mA}$	-	30	
Turn On Time	t_{on}		-	35	
Storage Time	t_s	$V_{CC}=30\text{V}, I_C=500\text{mA}$	-	50	ns
Fall Time	t_f	$I_{B1}=I_{B2}=50\text{mA}$	-	25	
Turn Off Time	t_{off}		-	60	

TO-39 Metal Can Package



All dimensions are in mm

DIM	MIN	MAX
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	—	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	—
L	42 DEG	48 DEG



PIN CONFIGURATION
1. EMITTER
2. BASE
3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20K	17" x 15" x 13.5"	32K	40 kgs

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered Trademark of

Continental Device India Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.

Telephone + 91-11-2579 6150, 5141 1112 Fax + 91-11-2579 5290, 5141 1119

email@cdil.com www.cdilsemi.com

2N3724_25Rev270901